Abstract of the Disclosure

## Circuit Arrangement

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A circuit arrangement is described having a terminal (1) for a high-frequency signal, having at least two additional signal leads (21a, 21b, 21c, 22a, 22b), having a switching unit (3) for connecting the terminal (1) to a signal lead (21a, 21b, 21c, 22a, 22b), having a primary protection device (41) against electrostatic discharges, which is connected between the terminal (1) and the switching unit (3), the protection device (41) containing a first voltage limitation element (51), which diverts voltage pulses that exceed a switching voltage of 200 V to a reference potential (7). The use of a gallium arsenide double diode makes it possible to attain the advantage of a low insertion loss coupled with a low switching voltage.

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Figure 1